High Current Transistors

NPN Silicon

Features

• These are Pb-Free Devices*

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector - Emitter Voltage BC637 BC638		60 80	Vdc
Collector - Base Voltage BC637 BC638		60 80	Vdc
Emitter - Base Voltage	V _{EBO}	5.0	Vdc
Collector Current - Continuous	I _C	1.0	Adc
Total Device Dissipation @ T _A = 25°C Derate above 25°C	P _D	625 5.0	mW mW/°C
Total Device Dissipation @ T _C = 25°C Derate above 25°C	P _D	800 12	mW mW/°C
Operating and Storage Junction Temperature Range	T _J , T _{stg}	-55 to +150	°C

THERMAL CHARACTERISTICS

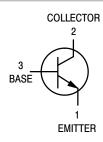
Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	200	°C/W
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	83.3	°C/W

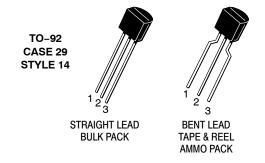
Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.



ON Semiconductor®

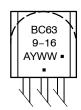
http://onsemi.com





MARKING DIAGRAMS





= 7 or 9

= Assembly Location

= Year = Work Week = Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

See detailed ordering and shipping information in the package

^{*}For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

ELECTRICAL CHARACTERISTICS ($T_A = 25^{\circ}C$ unless otherwise noted)

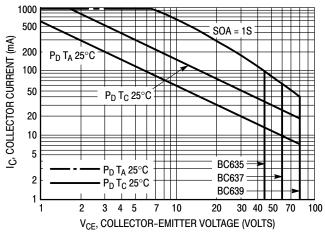
Characteristic					
Characteristic	Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS					
Collector – Emitter Breakdown Voltage (Note 1) $ (I_C = 10 \; \mu \text{Adc}, I_B = 0) \\ \text{BC63}; \\ \text{BC63}; $		60 80	- -	- -	Vdc
Collector – Emitter Zero–Gate Breakdown Voltage(Note 1) (I _C = 100 μAdc, I _B = 0) BC639–16	V _{(BR)CES}	120	_	-	Vdc
Collector – Base Breakdown Voltage (I _C = 100 μAdc, I _E = 0) BC633 BC636		60 80	- -	- -	Vdc
Emitter – Base Breakdown Voltage ($I_E = 10 \mu Adc, I_C = 0$)	V _{(BR)EBO}	5.0	_	_	Vdc
Collector Cutoff Current $(V_{CB} = 30 \text{ Vdc}, I_E = 0)$ $(V_{CB} = 30 \text{ Vdc}, I_E = 0, T_A = 125^{\circ}\text{C})$	Ісво	- -	- -	100 10	nAdc μAdc
ON CHARACTERISTICS (Note 1)					
DC Current Gain $ \begin{array}{l} \text{(I}_{C} = 5.0 \text{ mAdc, V}_{CE} = 2.0 \text{ Vdc)} \\ \text{(I}_{C} = 150 \text{ mAdc, V}_{CE} = 2.0 \text{ Vdc)} \\ \text{BC639} \\ \text{BC639} - 16\text{ZLT} \\ \text{(I}_{C} = 500 \text{ mA, V}_{CE} = 2.0 \text{ V)} \end{array} $	9	25 40 40 100 25	- - - -	- 160 160 250 -	-
Collector – Emitter Saturation Voltage (I _C = 500 mAdc, I _B = 50 mAdc)	V _{CE(sat)}	-	-	0.5	Vdc
Base – Emitter On Voltage (I _C = 500 mAdc, V _{CE} = 2.0 Vdc)	V _{BE(on)}	-	-	1.0	Vdc
DYNAMIC CHARACTERISTICS					
Current Gain – Bandwidth Product ($I_C = 50 \text{ mAdc}, V_{CE} = 2.0 \text{ Vdc}, f = 100 \text{ MHz}$)	f _T	-	200	-	MHz
Output Capacitance (V _{CB} = 10 Vdc, I _E = 0, f = 1.0 MHz)	C _{ob}	-	7.0	-	pF
Input Capacitance (V _{EB} = 0.5 Vdc, I _C = 0, f = 1.0 MHz)	C _{ib}	-	50	-	pF

^{1.} Pulse Test: Pulse Width \leq 300 $\mu s,$ Duty Cycle 2.0%.

ORDERING INFORMATION

Device	Package	Shipping [†]
BC637G	TO-92 (Pb-Free)	5000 Units / Bulk
BC637RL1G	TO-92 (Pb-Free)	2000 / Tape & Reel
BC639G	TO-92 (Pb-Free)	5000 Units / Bulk
BC639RL1G	TO-92 (Pb-Free)	2000 / Tape & Reel
BC639ZL1G	TO-92 (Pb-Free)	2000 / Ammo Box
BC639-16ZL1G	TO-92 (Pb-Free)	2000 / Ammo Box

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.



V_{CE}, COLLECTOR-EMITTER VOLTAGE (VOLTS)

Figure 1. Active Region Safe Operating Area

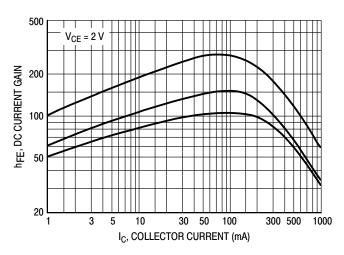


Figure 2. DC Current Gain

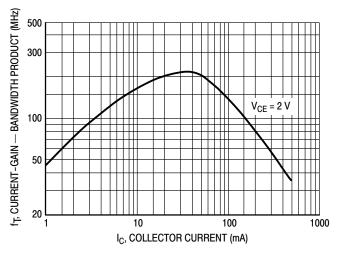


Figure 3. Current-Gain — Bandwidth Product

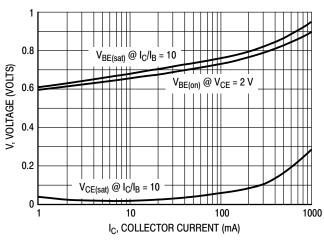


Figure 4. "Saturation" and "On" Voltages

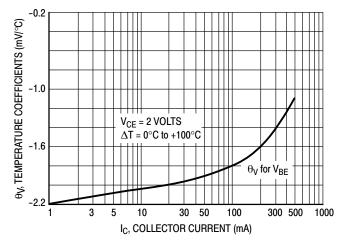
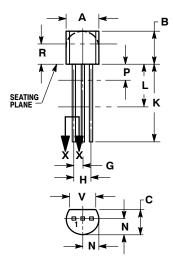


Figure 5. Temperature Coefficients

PACKAGE DIMENSIONS

TO-92 (TO-226) CASE 29-11 ISSUE AM

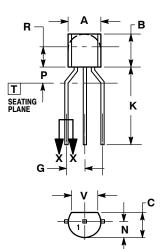


STRAIGHT LEAD **BULK PACK**



- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. CONTROLLING DIMENSION: INCH.
- CONTOUR OF PACKAGE BEYOND DIMENSION R
- IS UNCONTROLLED.
 LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

	INCHES		MILLIM	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.175	0.205	4.45	5.20
В	0.170	0.210	4.32	5.33
С	0.125	0.165	3.18	4.19
D	0.016	0.021	0.407	0.533
G	0.045	0.055	1.15	1.39
Н	0.095	0.105	2.42	2.66
J	0.015	0.020	0.39	0.50
K	0.500		12.70	
L	0.250		6.35	
N	0.080	0.105	2.04	2.66
P		0.100	-	2.54
R	0.115		2.93	
v	0 135		3 43	



BENT LEAD TAPE & REEL AMMO PACK



NOTES:

- DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
- CONTROLLING DIMENSION: MILLIMETERS. CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
- LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

	MILLIMETERS		
DIM	MIN	MAX	
Α	4.45	5.20	
В	4.32	5.33	
С	3.18	4.19	
D	0.40	0.54	
G	2.40	2.80	
J	0.39	0.50	
K	12.70		
N	2.04	2.66	
P	1.50	4.00	
R	2.93		
٧	3.43		

STYLE 14:

PIN 1. EMITTER

COLLECTOR

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